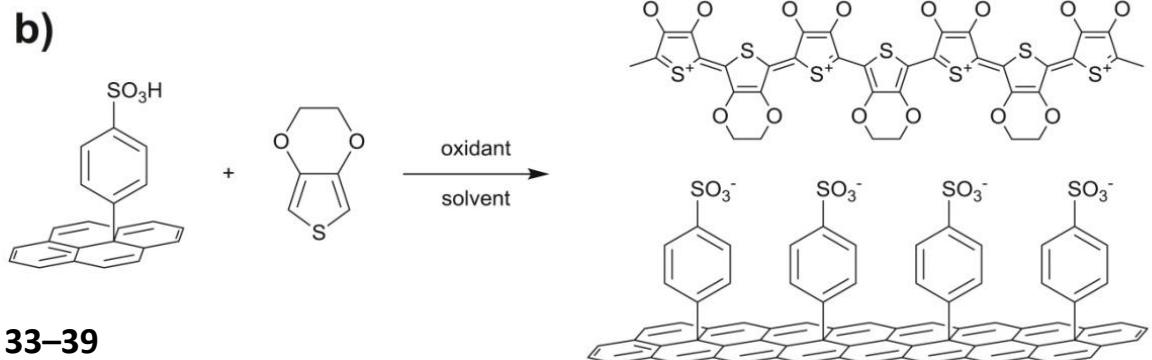
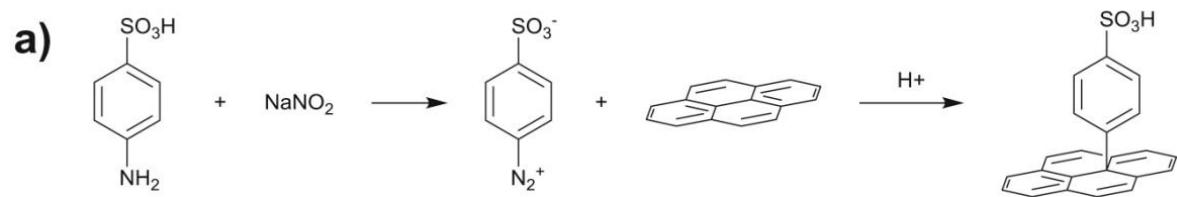


# Graphene as substrate for selective self-assembly of 2-D materials for optoelectronic applications

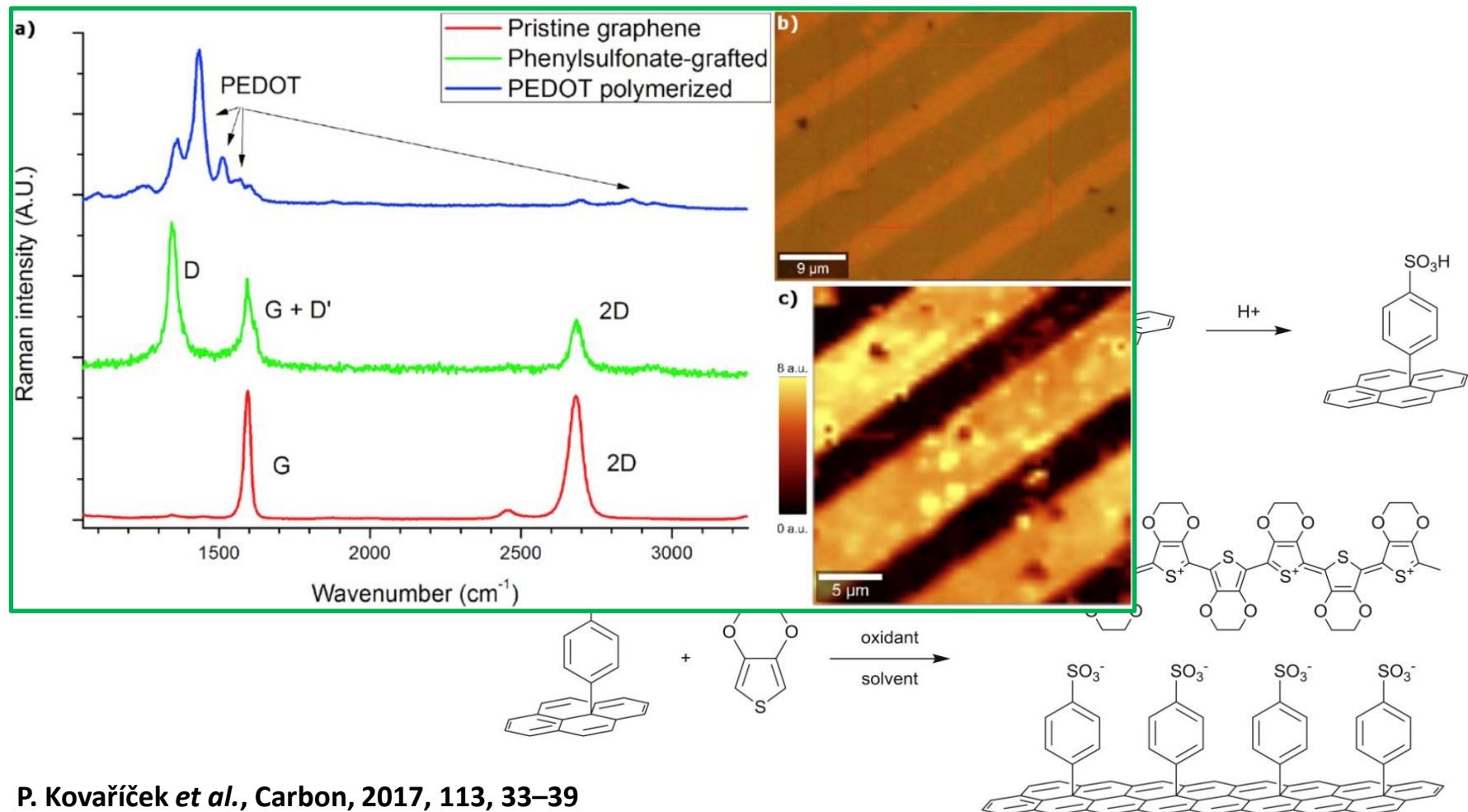
Valentino Libero Pio Guerra

# Functionalization of graphene and EDOT polymerization



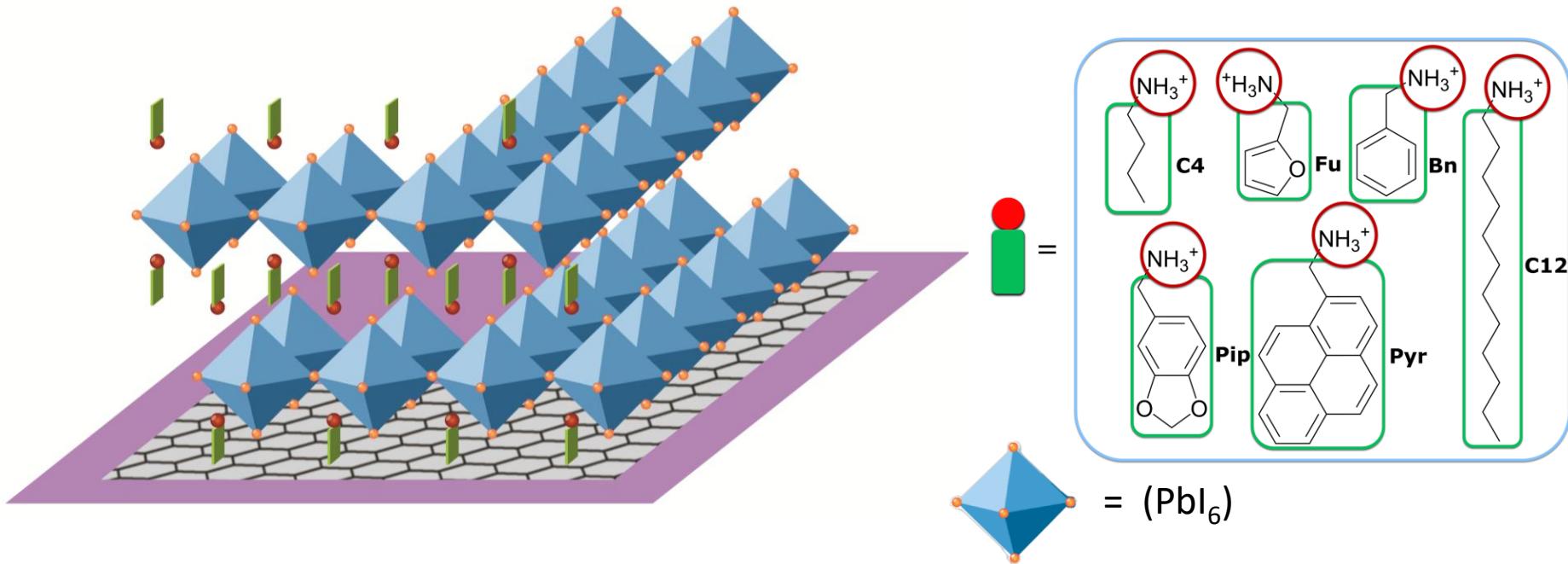
P. Kovaříček *et al.*, Carbon, 2017, 113, 33–39

# Functionalization of graphene and EDOT polymerization



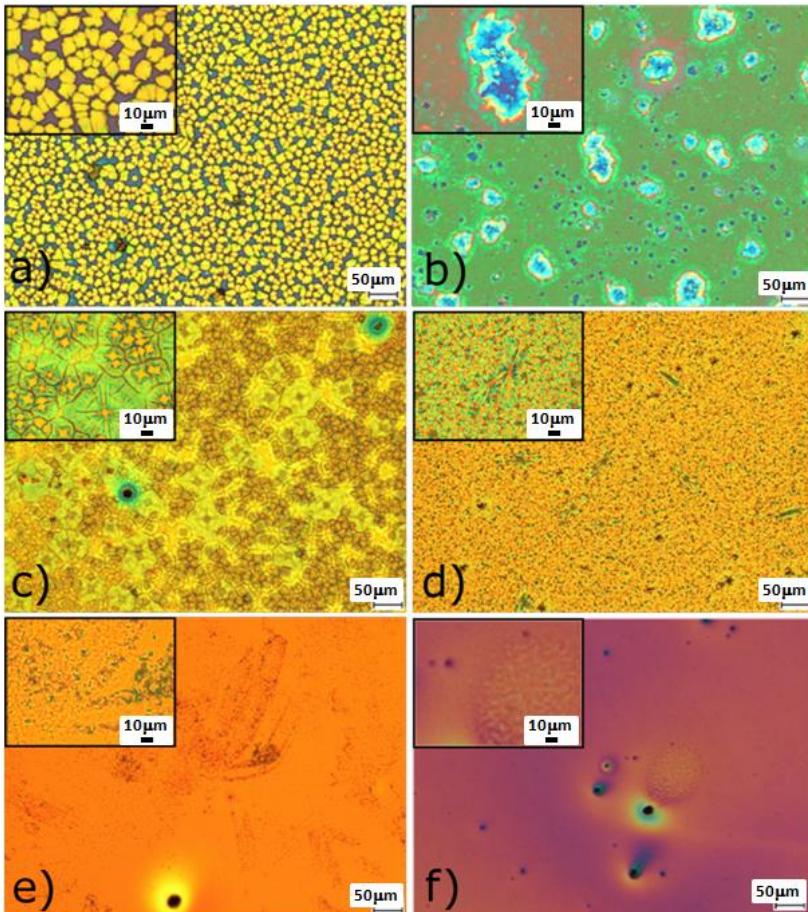
P. Kovaříček *et al.*, Carbon, 2017, 113, 33–39

# New material – choosing the precursors

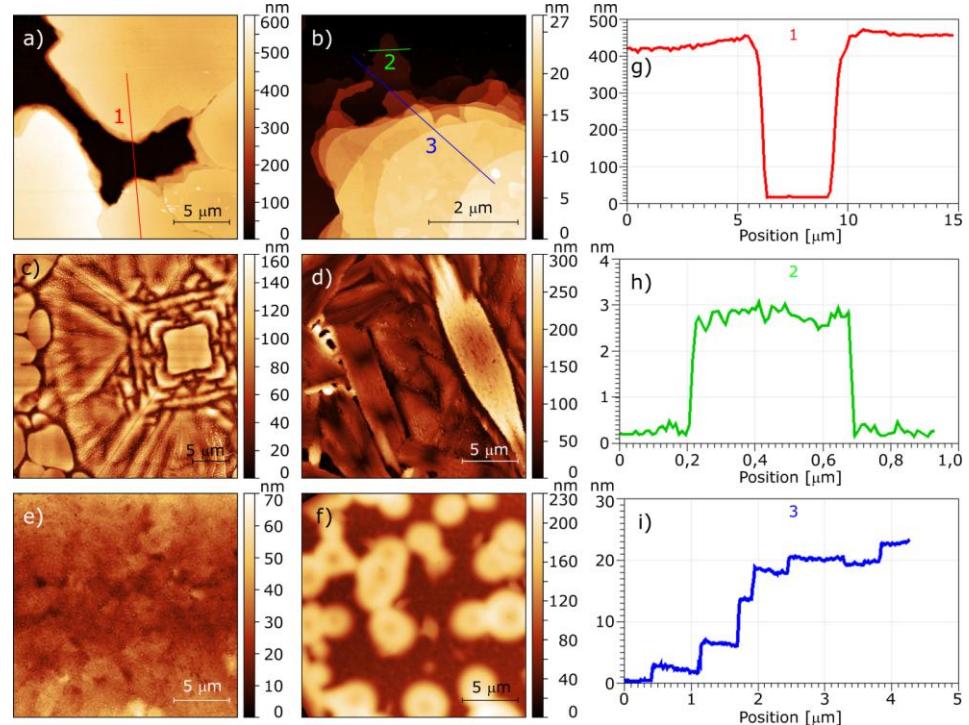


V. L. P. Guerra *et al.*, *Nanoscale*, 2018, 10, 3198-3211

# Morphology



Optical microscopy

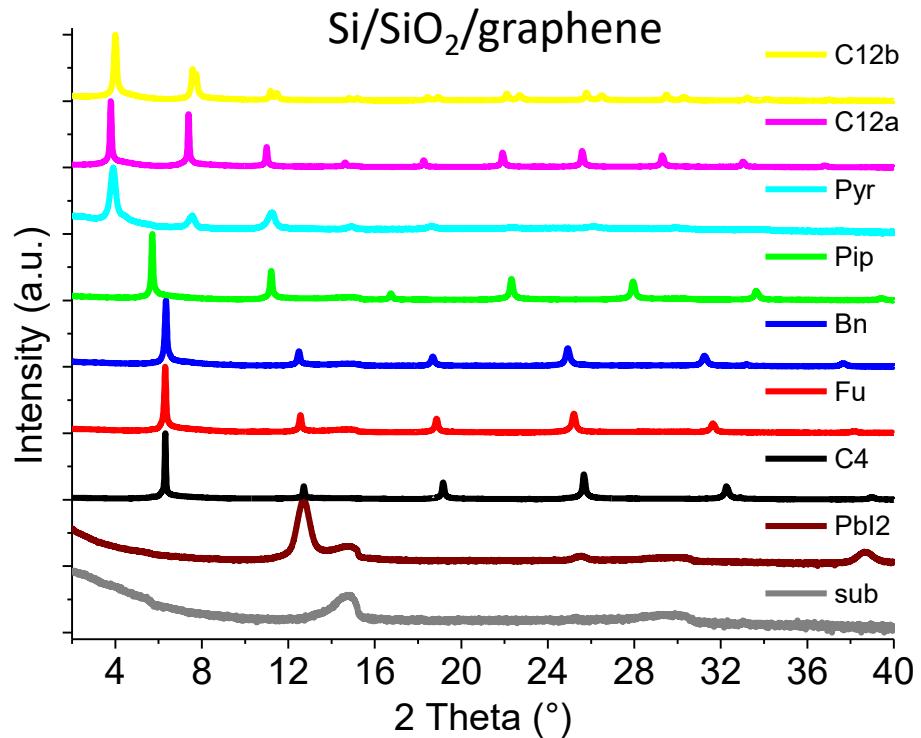
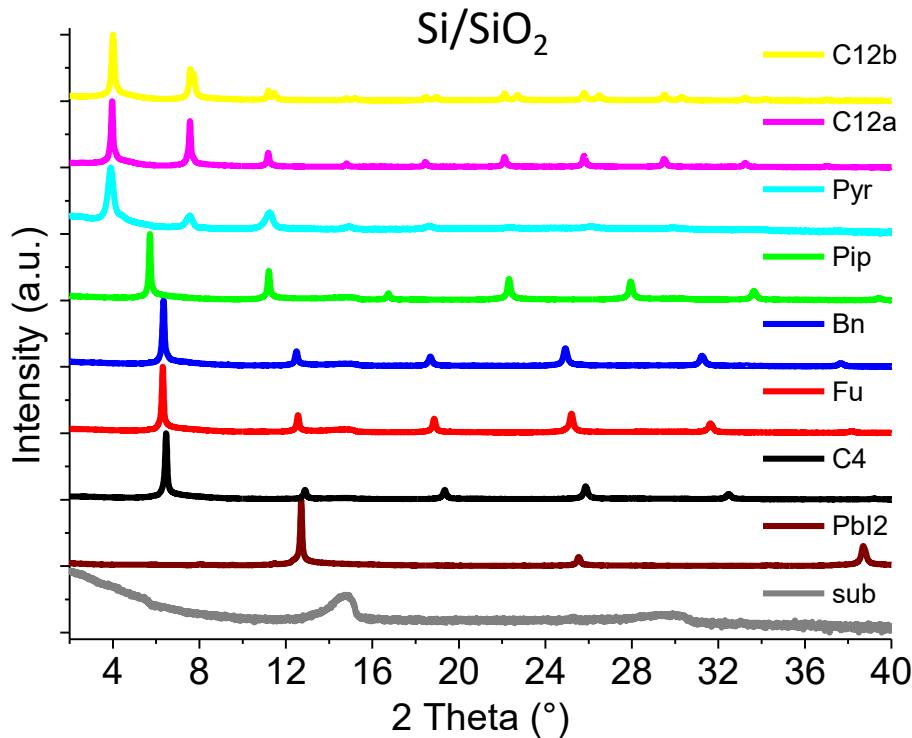


Atomic Force Microscopy

\*Oxygen plasma treated Si/SiO<sub>2</sub>

# Structure

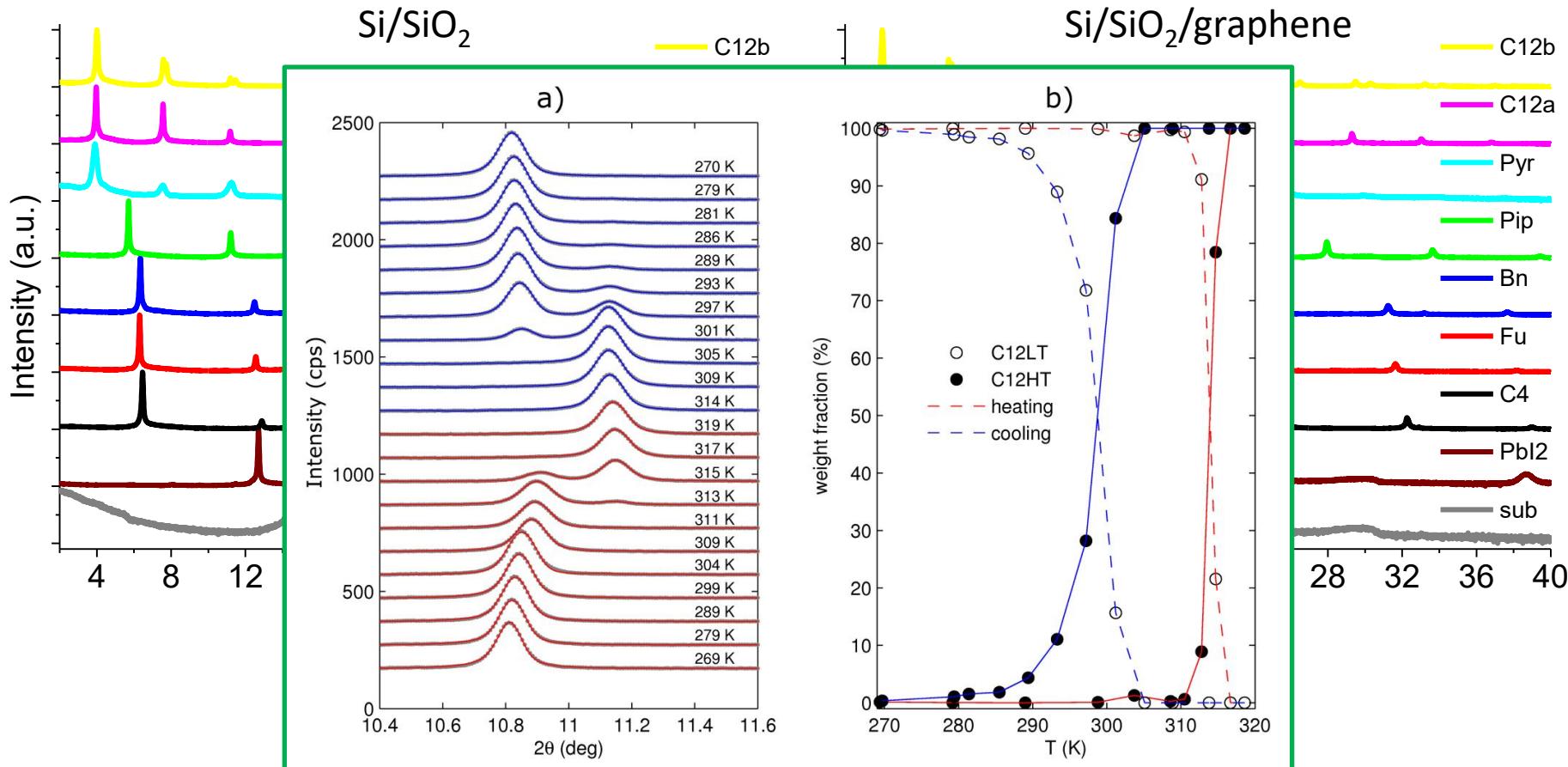
X-Ray Diffraction of the films on:



Only peaks corresponding to 00ℓ diffraction are visible → strong preferential orientation

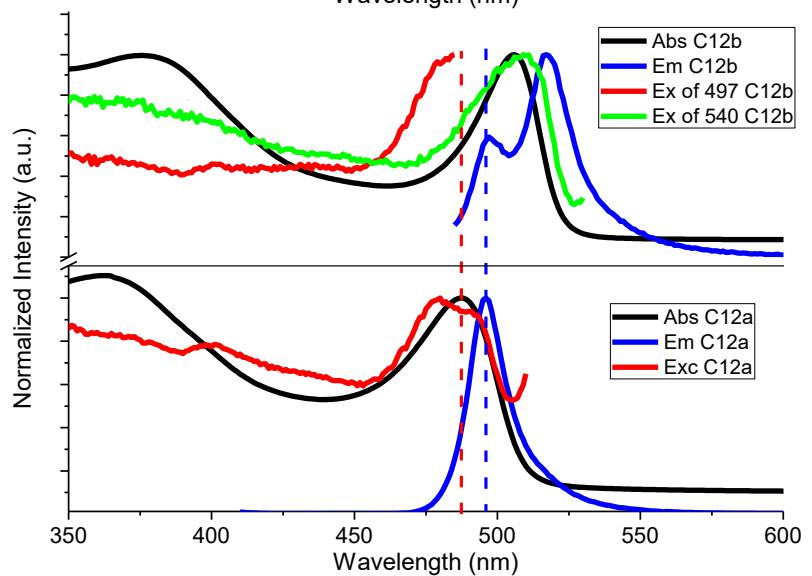
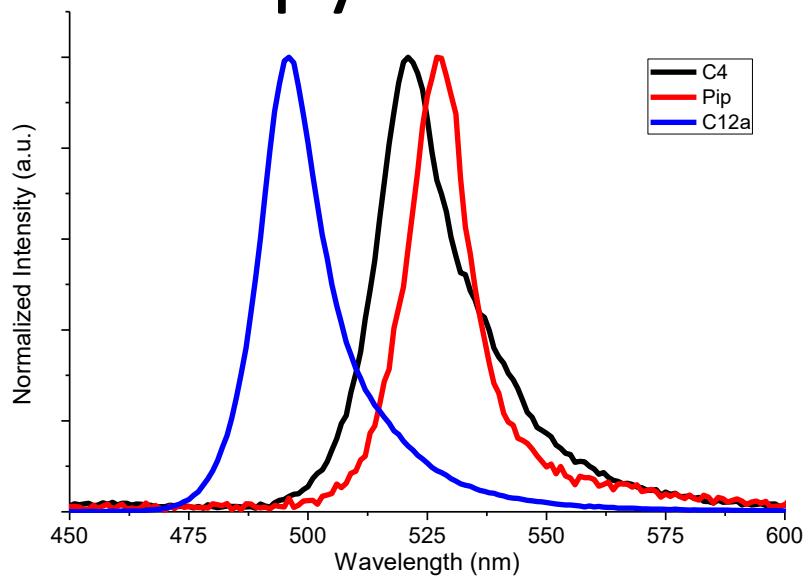
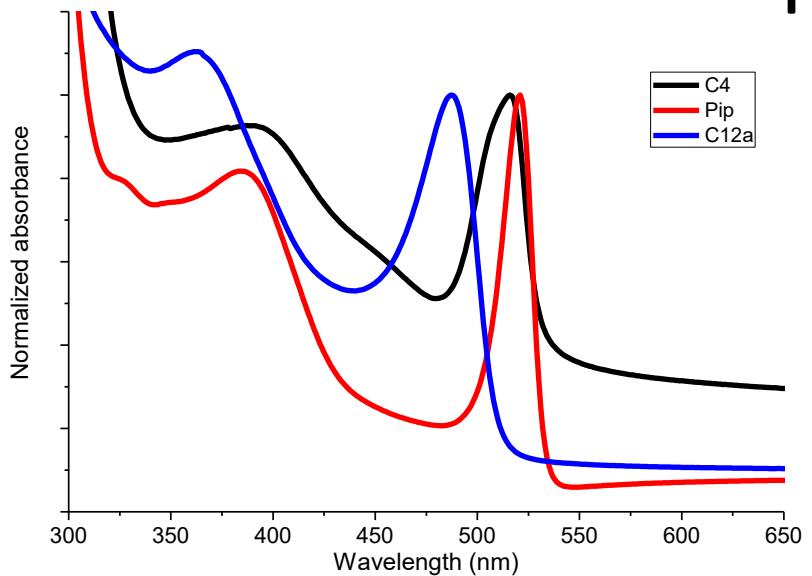
# Structure

X-Ray Diffraction of the films on:

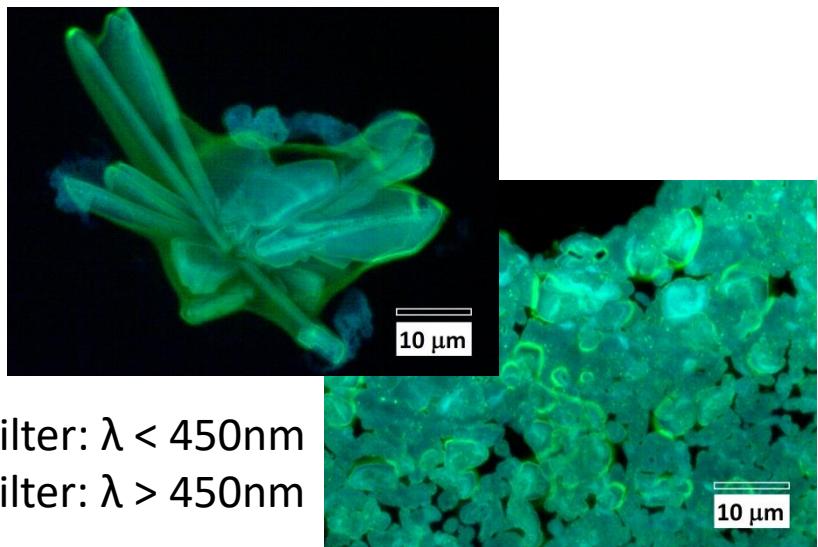


Only peaks corresponding to 00 $\ell$  diffraction are visible → strong preferential orientation

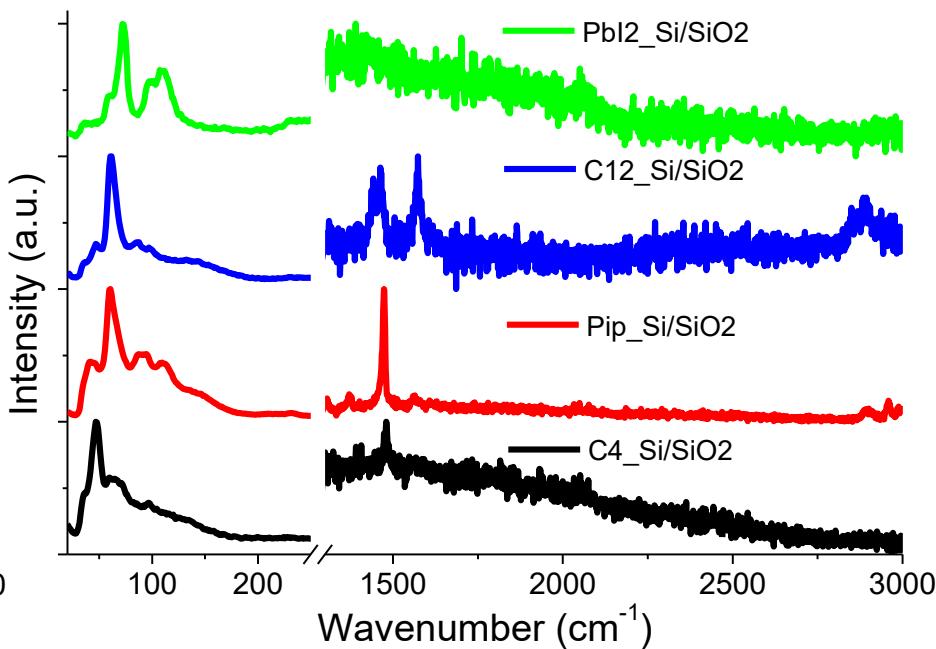
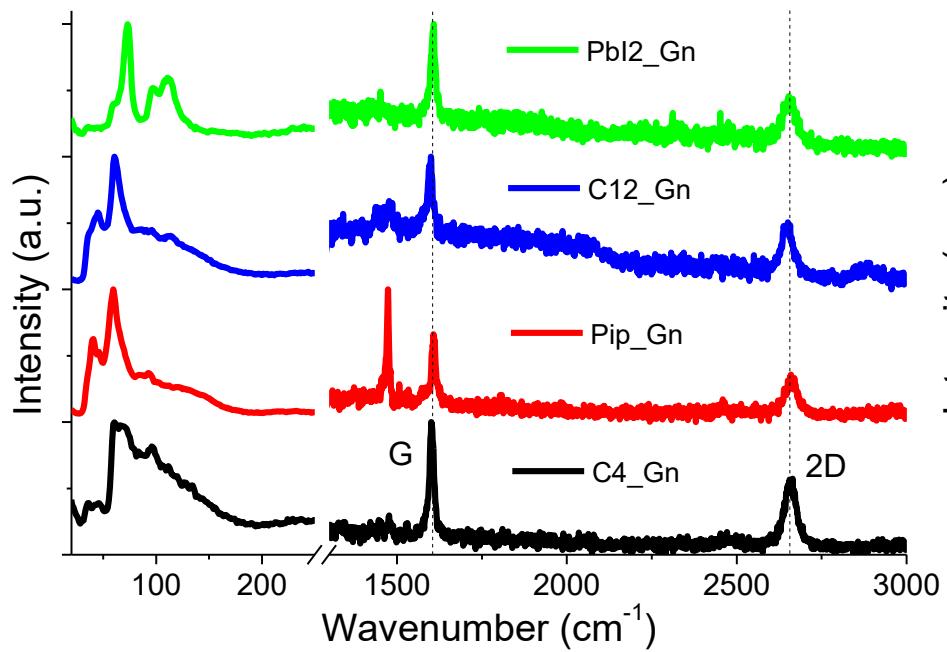
# Uv-vis spectroscopy



Ex filter:  $\lambda < 450\text{nm}$   
Em filter:  $\lambda > 450\text{nm}$



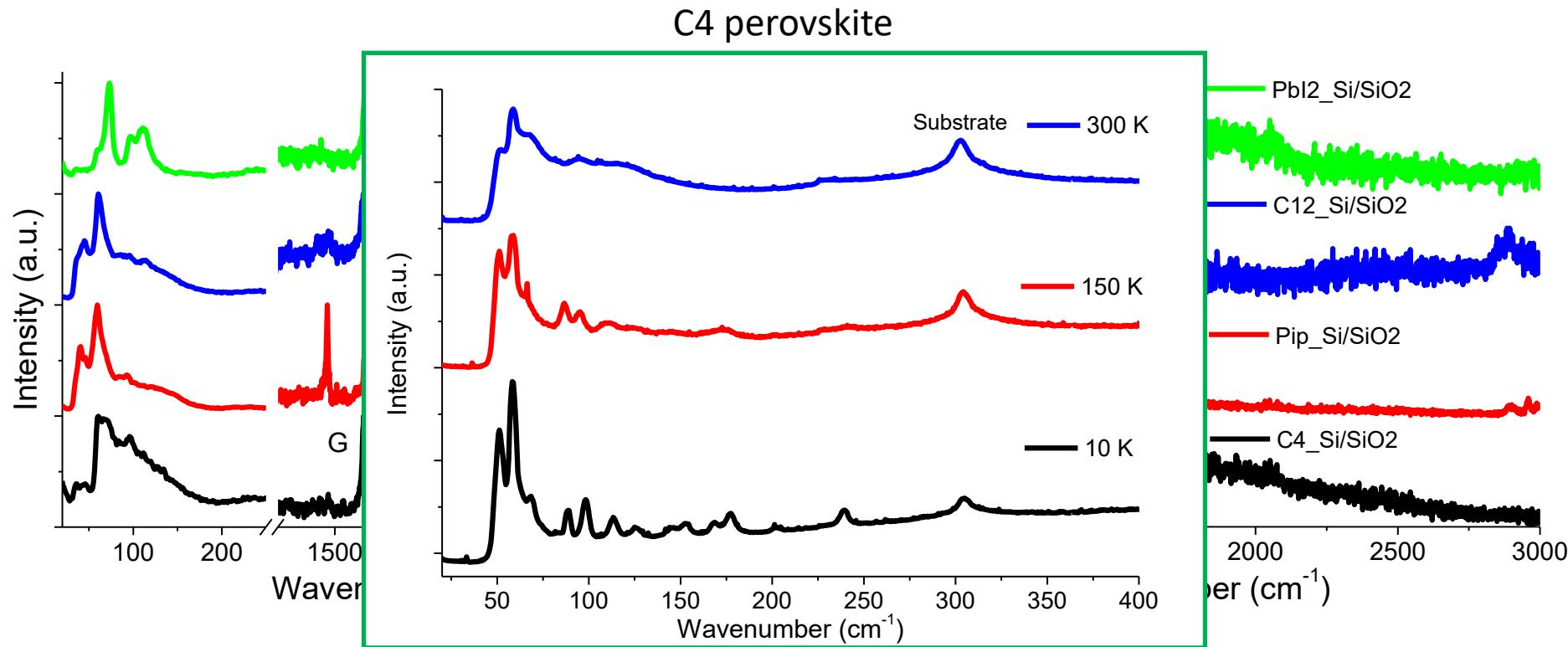
# Raman spectroscopy



Low wavenumber region: vibrational fingerprint of Pb-I network

High wavenumber region: 1470 cm<sup>-1</sup> CH<sub>2</sub> scissoring, 1600 cm<sup>-1</sup> G mode, 2650 cm<sup>-1</sup> 2D mode

# Raman spectroscopy

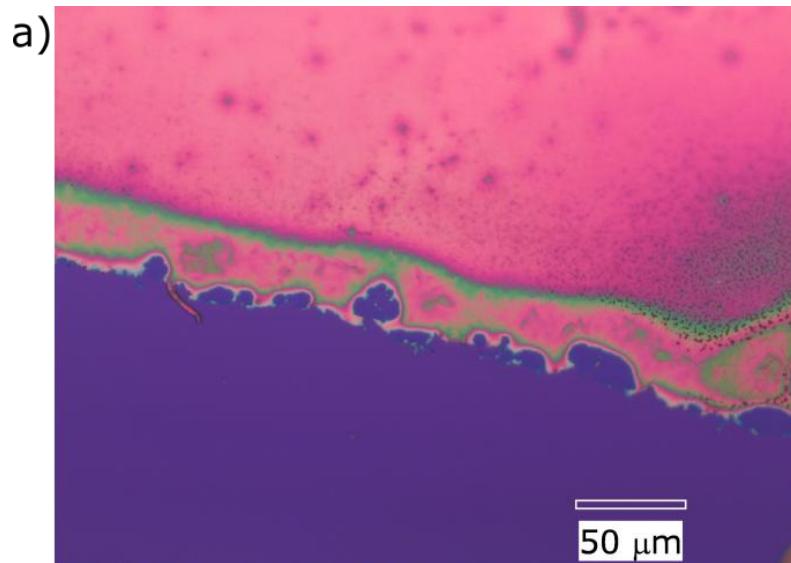


Low wavenumber region: vibrational fingerprint of Pb-I network

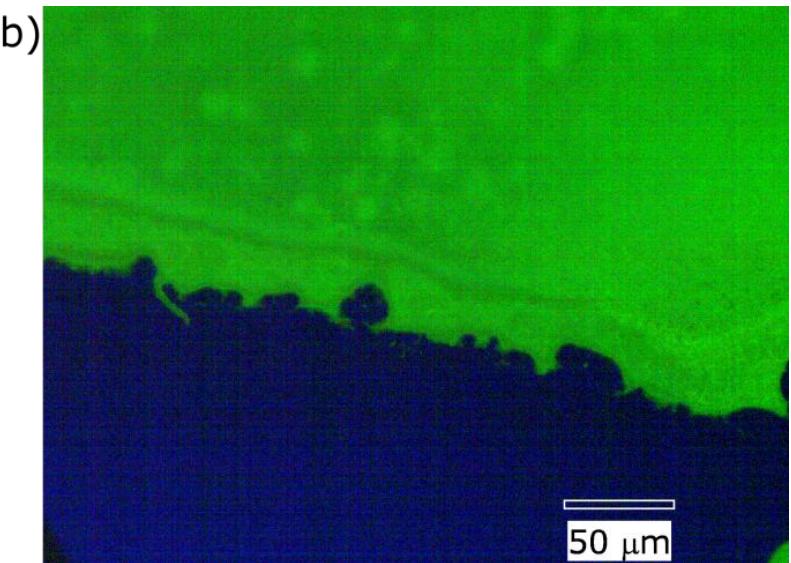
High wavenumber region: 1470 cm<sup>-1</sup> CH<sub>2</sub> scissoring, 1600 cm<sup>-1</sup> G mode, 2650 cm<sup>-1</sup> 2D mode

# Selectivity of the assembly

Optical microscopy



Bright field

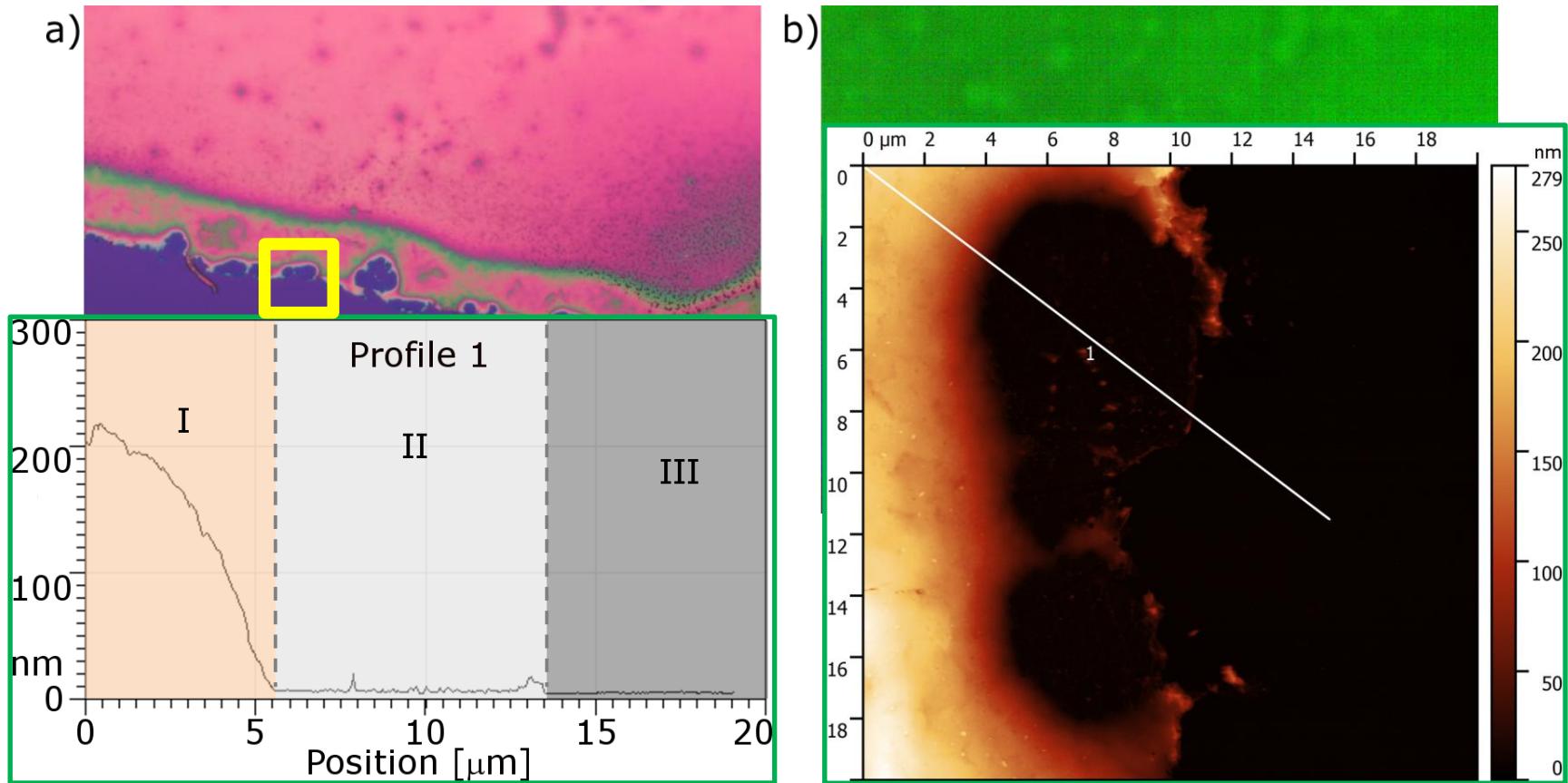


Ex filter:  $\lambda < 450\text{nm}$   
Em filter:  $\lambda > 450\text{nm}$

Pip perovskite spincoated on graphene

# Selectivity of the assembly

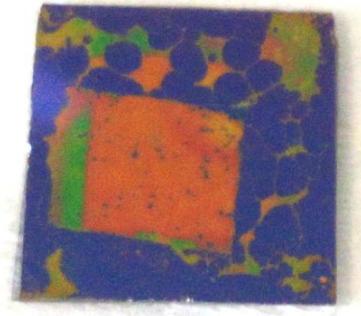
AFM



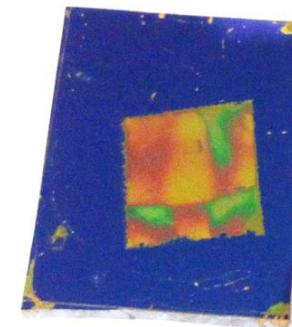
# Selectivity of the assembly



Si/SiO<sub>2</sub>



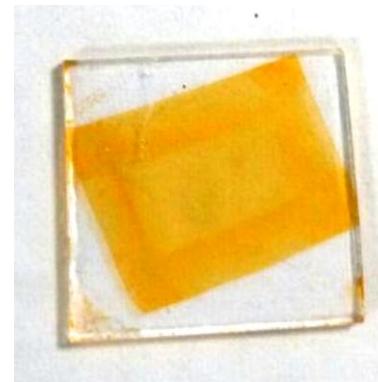
Gn @ Si/SiO<sub>2</sub>



Gn @ endcapped Si/SiO<sub>2</sub>

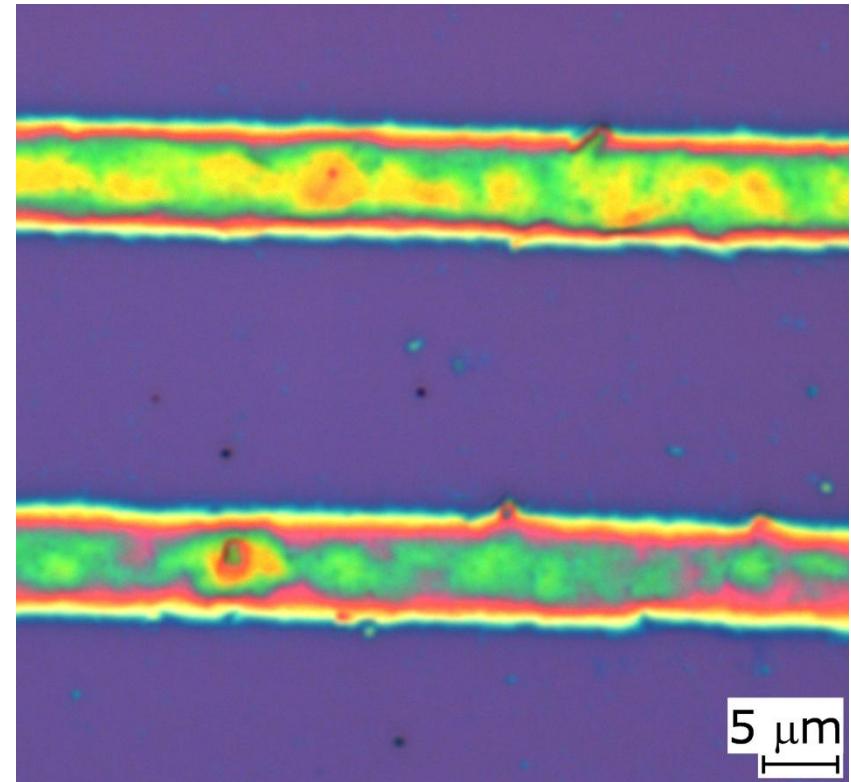
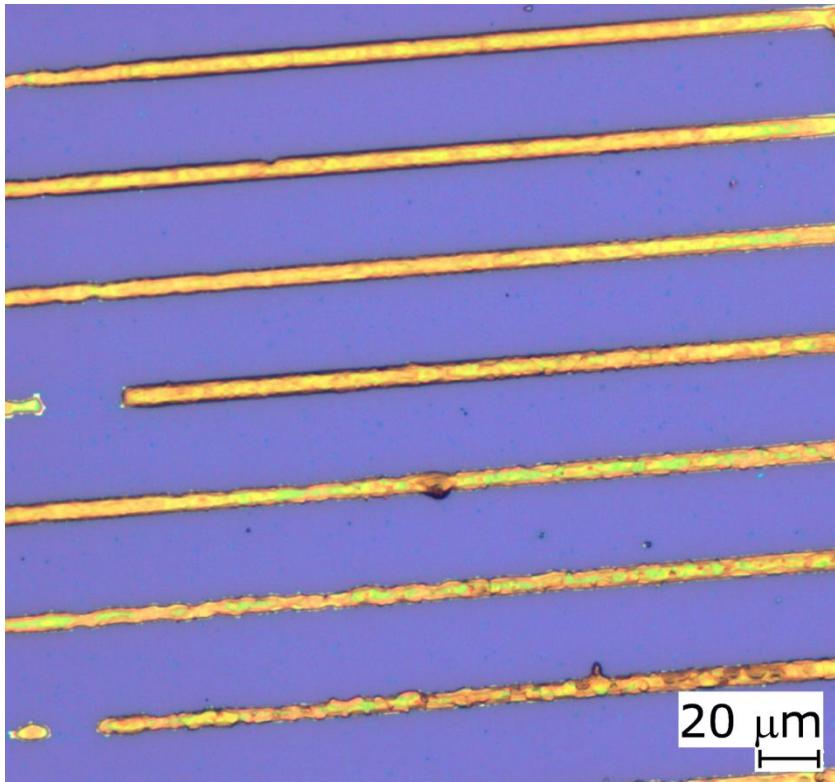


Oxygen plasma treated glass



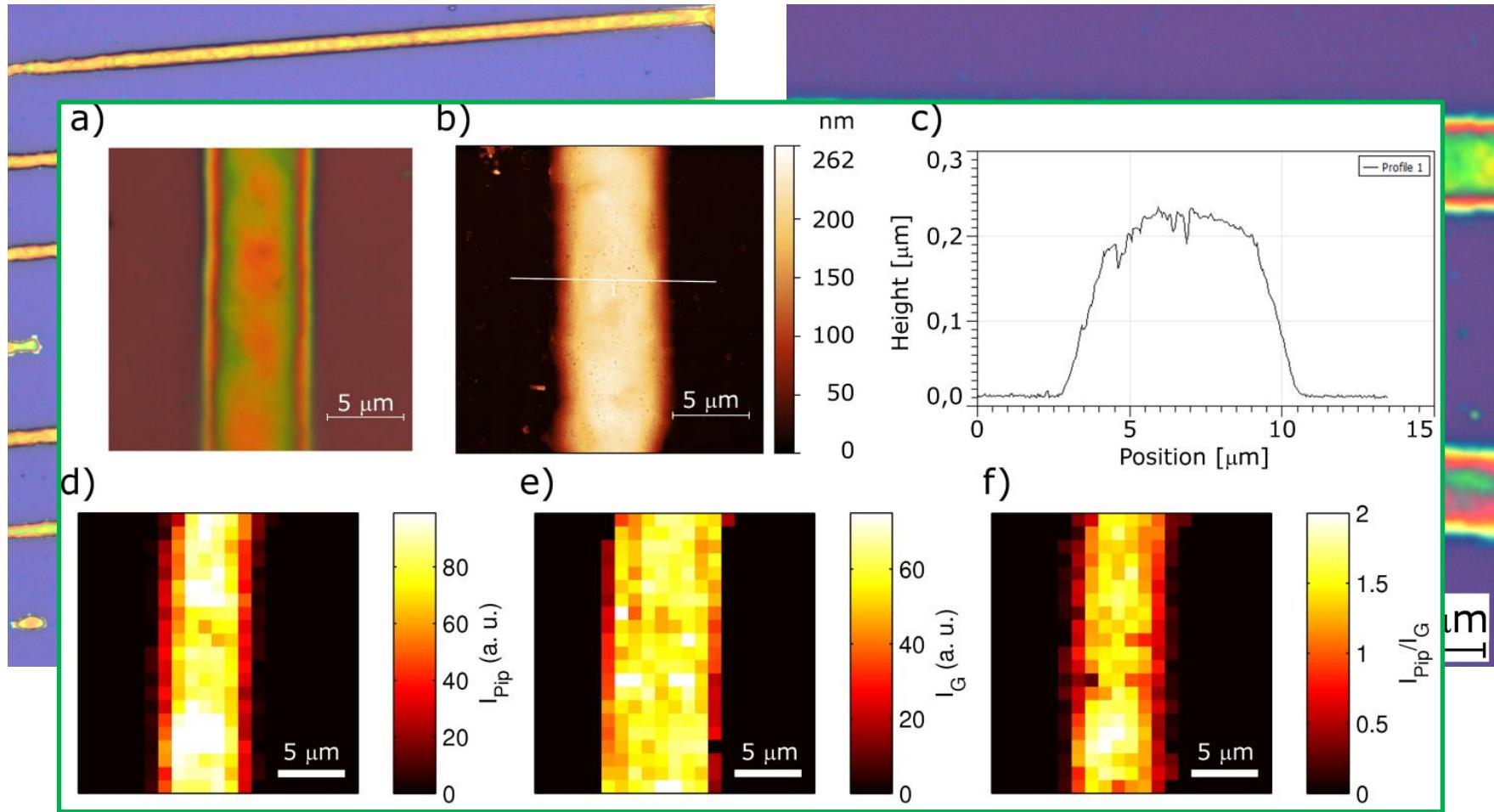
Gn @ Glass

# Selectivity of the assembly



Pip perovskite spincoated on photolithographically patterned graphene

# Selectivity of the assembly

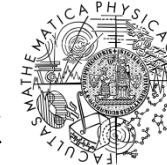


# Summary

- Library of perovskites with characterization of their properties
- Preferential growth achieved by simple choice of precursors
- High spatial resolution of the selective self-assembly

# Acknowledgements

- J. Heyrovský Institute of Physical Chemistry of the Czech Academy of Sciences (Prague, Czech Republic)
  - Petr Kovaříček, Václav Valeš, Karolina Drogowska, Martin Kalbáč
- Department of Condensed Matter Physics, Faculty of Mathematics and Physics, Charles University (Prague, Czech Republic)
  - Tim Verhagen, Jana Vejpravova, Lukáš Horák
- Istituto di Nanotecnologia CNR-Nanotec, Polo di Nanotecnologia (Lecce, Italy)
  - Andrea Listorti, Silvia Colella



FACULTY  
OF MATHEMATICS  
AND PHYSICS  
Charles University

